**ma-N 400 and ma-N 1400 - Negative Tone Photoresists**

**Unique features**
- High wet and dry etch resistance
- Good thermal stability of the resist pattern
- Tunable pattern profile: vertical to undercut
- Aqueous alkaline development
- Easy to remove
- Resists available in a variety of viscosities

**Applications**
- Microelectronics and micro systems technology
- Mask for lift-off processes
- Etch mask for semiconductors and metals
- Well suitable for implantation

**Standard and Lift-off process flow**

**Technical data**

<table>
<thead>
<tr>
<th>Resist</th>
<th>ma-N 400 µm</th>
<th>ma-N 1400 µm</th>
</tr>
</thead>
<tbody>
<tr>
<td>Film thickness</td>
<td>ma-N 405 0.5</td>
<td>ma-N 1405 0.5</td>
</tr>
<tr>
<td></td>
<td>ma-N 415 1.5</td>
<td>ma-N 1407 0.7</td>
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<tr>
<td></td>
<td>ma-N 420 2.0</td>
<td>ma-N 1410 1.0</td>
</tr>
<tr>
<td></td>
<td>ma-N 440 4.1</td>
<td>ma-N 1420 2.0</td>
</tr>
<tr>
<td></td>
<td>ma-N 490 7.5</td>
<td>ma-N 1440 4.0</td>
</tr>
</tbody>
</table>

Spin coating: 3000 rpm; 30 s

Spectral sensitivity: 300 - 380 nm

Thermal stability: Up to 110 °C, for metal evaporation; Up to 160 °C, for metal evaporation and sputtering